

Substitute for form 1449/PTO		Application Number	10/525,297
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Filing Date	02/15/2005
(Use as many sheets as necessary)		Inventor(s)	James S. Im
		Art Unit	2822
		Examiner Name	Bac H. Au
		Attorney Docket Number	070050.2717

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	57.	6577380	6/10/2003	Sposili, Robert S. ; Farmiga, Nestor O. ; Jain, Kanti
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	63.	6635932	10/21/2003	Grigoropoulos, Costas P. ; Hatano, Mutsuko ; Lee, Ming Hong ; Moon, Seung Jae
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	65.	6667198	12/23/2003	Shimoto, Shigeyuki ; Uchikoga, Shuichi
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	76.	20040224487	11/11/2004	Yang, Myoung Su
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	78.	20050059265	3/17/2005	Im, James
	79.	6908835	6/21/2005	Sposili, Robert S. ; Im, James S.
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	81.	20050142450	6/30/2005	Jung, Yun
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	83.	20050202654	9/15/2005	Im, James
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	88.	7091411	8/15/2006	Falk, Fritz ; Andrae, Gudrun
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	91.	20070007242	1/11/2007	Im, James
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	94.	7187016	3/6/2007	Arima, Yutaka
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Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)	
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		Art Unit	2822
		Examiner Name	Bac H. Au
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